



100V N-Channel Power MOSFET

TO-252 (DPAK)



Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
100	37 @ V _{GS} =10V	32

Features

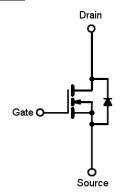
- Advanced Trench Technology
- Low $R_{DS(ON)} 37m\Omega$ (Max.)
- Low gate charge typical @ 34nC (Typ.)
- Low Crss typical @ 45pF (Typ.)

Ordering Information

Ordering code	Package	Packing
TSM35N10CP ROG	TO-252	2.5Kpcs / 13" Reel

Note: Halogen-free according to IEC 61249-2-21 definition

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	100	V	
Gate-Source Voltage		V_{GS}	±20	V	
	T _C =25°C		32		
Continuous Drain Correct	T _C =70°C] ,	26	Α	
Continuous Drain Current	T _A =25°C	- I _D	5		
	T _A =70°C		4		
Drain Current-Pulsed Note 1		I _{DM}	70	Α	
Avalanche Current, L=0.1mH		I _{AS} , I _{AR}	35	Α	
Avalanche Energy, L=0.1mH		E _{AS} , E _{AR}	61	mJ	
	T _C =25°C		83.3		
Maximum Dawar Dissination	T _C =70°C		53.3	W	
Maximum Power Dissipation	T _A =25°C	P _D	2		
	T _A =70°C		1.3	ı	
Storage Temperature Range		T _{STG}	-55 to +150	°C	
Operating Junction Temperature Range		T _J	-55 to +150	°C	

^{*} Limited by maximum junction temperature

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	$R\Theta_{JC}$	1.5	°C/W
Thermal Resistance - Junction to Ambient	$R\Theta_{JA}$	62	°C/W



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Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	100			V
	$V_{GS} = 10V, I_{D} = 10A$	R _{DS(ON)}		30	37	mΩ
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 10A$	R _{DS(ON)}		32	42	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	1	2	3	V
Zero Gate Voltage Drain Current	$V_{DS} = 100V, V_{GS} = 0V$	I _{DSS}			1	uA
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Dynamic						
Total Gate Charge	$V_{DS} = 50V, I_{D} = 10A,$	Qg		34		
Gate-Source Charge		Q _{gs}		6		nC
Gate-Drain Charge	$V_{GS} = 10V$	Q_gd		9		
Input Capacitance		C _{iss}		1598		
Output Capacitance	$V_{DS} = 30V, V_{GS} = 0V,$	C _{oss}		132		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		45		
Switching						
Turn-On Delay Time		t _{d(on)}		7		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 50V,$ $R_{G} = 3\Omega$	t _r		7		0
Turn-Off Delay Time		t _{d(off)}		29		nS
Turn-Off Fall Time		t _f		7		
Drain-Source Diode Characteristics and Maximum Rating						
Drain-Source Diode Forward Voltage	V _{GS} =0V, I _S =10A	V _{SD}		0.7		V
Reverse Recovery Time	I _S = 10A, T _J =25 °C	t _{fr}		32		nS
Reverse Recovery Charge	dI/dt = 500A/us	Q_{fr}		200		nC

Notes:

- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2. $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JC}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design.

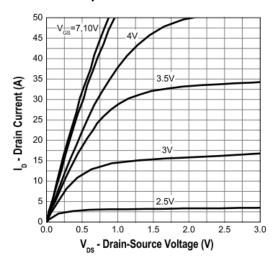


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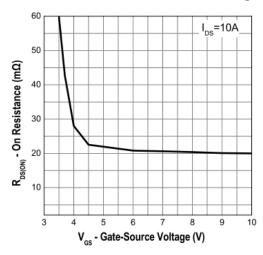


Electrical Characteristics Curve (Tc = 25°C, unless otherwise noted)

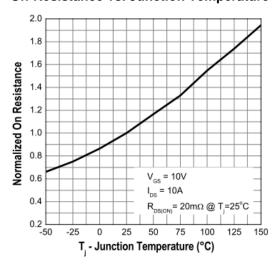
Output Characteristics



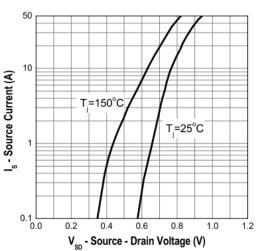
On-Resistance vs. Gate-Source Voltage



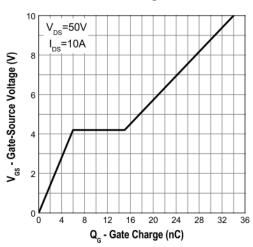
On-Resistance vs. Junction Temperature



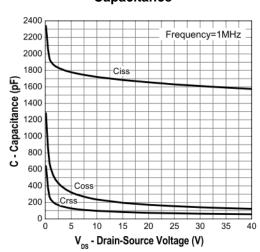
Transfer Characteristics



Gate Charge



Capacitance



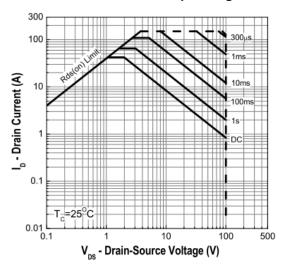


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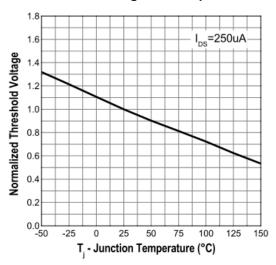


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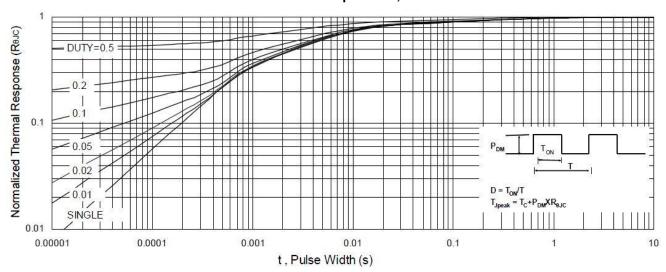
Maximum Safe Operating Area



Threshold Voltage vs. Temperature



Normalized Thermal Transient Impedance, Junction-to-Ambient



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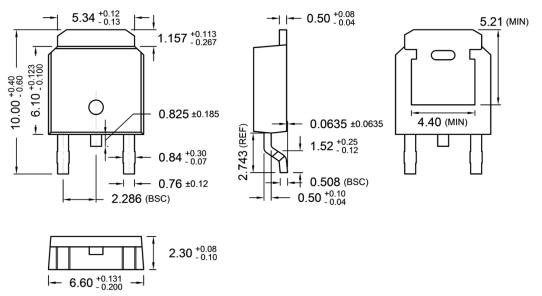
Version: C1807



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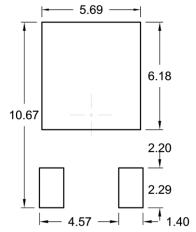


TO-252 Mechanical Drawing



Unit: Millimeters

SUGGESTED PAD LAYOUT (Unit: Millimeters)



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Marking Diagram



Version: C1807



TSM35N10CP 100V N-Channel Power MOSFET

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